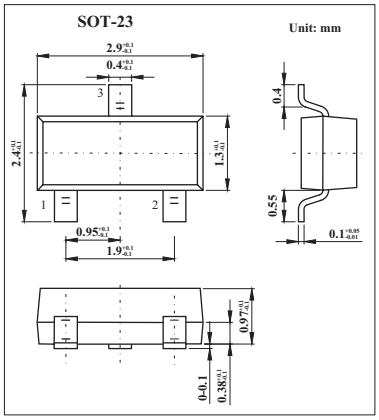
TY Semicondutor®

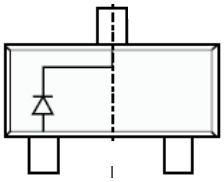
Product specification

KAT750(BAT750)



■ Features

- Very Low Forward Voltage Drop
- High Conductance
- For Use in DC-DC Converter, PCMCIA, and Mobile Telecommunications Applications



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Peak repetitive reverse voltage Working peak reverse voltage DC blocking voltage	V_{RRM} V_{RWM} V_R	40	V
RMS reverse voltage	$V_{R(RMS)}$	28	V
Average rectified output current	I_O	0.75	A
Non-Repetitive Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	5.5	A
Power dissipation	P_D	350	mW
Typical Thermal Resistance Junction to Ambient	$R_{\theta JA}$	286	℃/W
Operating and storage temperature range	T_j,T_{stg}	-40 to +125	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	I_R = 300 μ A	40	45		V
Forwarad voltage	V_F	I_F = 50mA		225	280	mV
		I_F = 100mA		235	310	
		I_F = 250mA		290	350	
		I_F = 500mA		340	420	
		I_F = 750mA		390	490	
		I_F = 1000mA		420	540	
		I_F = 1500mA		475	650	
Leakage current	I_R	V_R = 15V		50	100	μ A
Junction Capacitance	C_J	V_R = 0, f = 1.0MHz		175		pF
		V_R = 25V, f = 1.0MHz		25		

■ Marking

Marking	K77 or K79